

Figure 2. RHEED pattern of (a) (110) substrate and (b) (010) substrate after Ga polishing

Figure 3. HRXRD patterns of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> films grown on (110) substrate

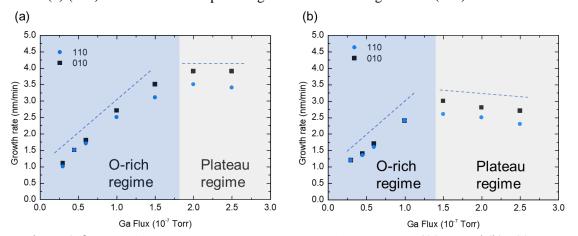


Figure 4. β-Ga<sub>2</sub>O<sub>3</sub> films grown on (110) and (010) substrates at (a) 600 °C and (b) 700 °C

Ga flux	6.0 ×	10 <sup>-8</sup> Torr	1.0 ×	10 <sup>-7</sup> Torr	1.5 ×	10 <sup>-7</sup> Torr	2.0 ×	10 <sup>-7</sup> Torr	2.5 ×	10 <sup>-7</sup> Torr
Croudh	17.8 nm	0.0 nm	20.3 nm	0.0 nm	5.6 nm	0.0 nm	5.7 nm	0.0 nm	3.2 nm	0.0 nm
Growth on (110)	RMS: 2.0	J nm	RMS: 2.2	nm	RMS: 0	7 mm	RMS: 0.8	nni	RMS: 0	.4 nm
sub.		Spm.		Zum		Carth		2,m		- <u>- 1</u>
Growth on (010) sub.	16.9 nm	AT MICH SHE SHOULD	15.2 nm	0.0 nm	9.3 nm RMS: J	SAN EL PONOPPE A	10.3 nm	0.0 nm	6.0 nm RMS; 0	0.0 nm

Figure 5. AFM images of β-Ga<sub>2</sub>O<sub>3</sub> films grown on (110) and (010) substrates at 700 °C